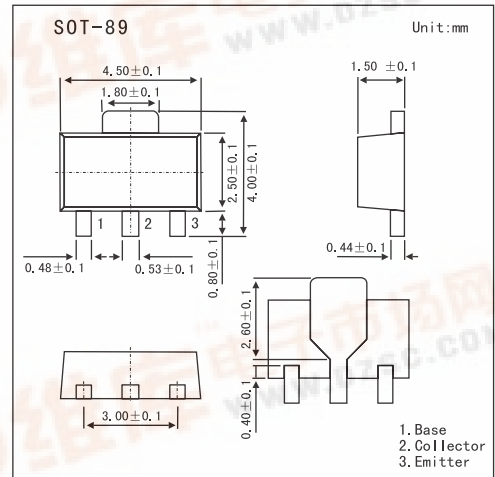


SMD Type Transistors

PNP Silicon Power Switching Transistor
FCX789A

■ Features

- 2W power dissipation.
- 8A peak pulse current.
- Excellent HFE characteristics up to 10 Amps.
- Extremely low saturation voltage E.g. 10mv Typ.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-25	V
Collector-emitter voltage	V _{CE0}	-25	V
Emitter-base voltage	V _{EB0}	-5	V
Continuous collector current	I _{CM}	-8	A
Peak pulse current	I _c	-3	A
Power dissipation	P _{tot}	1	W
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

FCX789A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-25			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector cut-off current	ICBO	VCB=-10V			0.1	μA
Emitter Cut-Off Current	IEBO	VEB=-4V			0.1	μA
Collector-emitter saturation voltage *	VCE(sat)	IC=-1A, IB=-10mA IC=-2A, IB=-20mA IC=-3A, IB=-100mA			-190 -400 -320	mV
Base-emitter saturation voltage *	VBE(sat)	IC=-1A, IB=-10mA			-0.9	V
Base-emitter ON voltage *	VBE(on)	IC=-1A, VCE=-2V		-0.8		V
Static Forward Current Transfer Ratio *	hFE	IC=-10mA, VCE=-2V IC=-1A, VCE=-2V IC=-2A, VCE=-2V IC=-6A, VCE=-2V	300 230 180 75	800		
Transitional frequency	fT	IC=-50mA, VCE=-5V, f=50MHz	100			MHz
Input capacitance	Cibo	VEB=-0.5V, f=1MHz		225		pF
Output capacitance	Cobo	VCB=-10V, f=1MHz		25		pF
Turn-on time	t(on)	IC=-500mA, VCC=-10V		35		ns
Turn-off time	t(off)	IB1=IB2=-50mA		400		ns

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	789
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